WHAT IS CLAIMED IS:

ı	1. A thin film transistor array panel comprising:
2	a substrate;
3	a gate line formed on the substrate and including a gate electrode;
4	a gate insulating layer formed on the gate line;
5	a semiconductor layer formed on the gate insulating layer;
6	a data line formed at least in part on the semiconductor layer;
7	a drain electrode formed on the semiconductor layer at least in part and separated from
8	the data line;
9	a first passivation layer formed on the data line and the drain electrode;
10	a first protrusion formed on the first passivation layer and disposed opposite the data line
11	and
12	a pixel electrode formed on the first passivation layer and connected to the drain
13	electrode.
	 The thin film transistor array panel of claim 1, wherein the pixel electrode has a
1	
2	cutout.
1	3. The thin film transistor array panel of claim 2, further comprising a second
2	protrusion disposed in the cutout.
1	4. The thin film transistor array panel of claim 2, further comprising a storage
2	electrode line overlapping the pixel electrode.

5. The thin film transistor array panel of claim 4, wherein the storage electrode line 1 comprises an expansion overlapping the drain electrode. 2 6. The thin film transistor array panel of claim 4, wherein the storage electrode line 1 comprises a branch overlapping the cutout. 2 The thin film transistor array panel of claim 1, wherein the first protrusion is 7. ı wider than the data line. 2 The thin film transistor array panel of claim 1, wherein the data line is curved. 8. 9. The thin film transistor array panel of claim 1, further comprising a spacer having ı a height larger than the first protrusion and disposed on the same layer as the first protrusion. 2 10. The thin film transistor array panel of claim 9, wherein the first protrusion and the spacer comprise organic material. 2 11. The thin film transistor array panel of claim 1, further comprising a color filter 1 disposed between the first passivation layer and the first protrusion and the pixel electrode. 2 12. The thin film transistor array panel of claim 11, further comprising a second ı passivation layer formed on the color filter and the first protrusion and the pixel electrode. 1 13. The thin film transistor array panel of claim 1, wherein the semiconductor layer

has substantially the same planar shape as the data line and the drain electrode.

- 14. A thin film transistor array panel comprising: ı a substrate; a gate line formed on the substrate and including a gate electrode; 3 a gate insulating layer formed on the gate line; a semiconductor layer formed on the gate insulating layer; 5 a data line formed at least in part on the semiconductor layer; a drain electrode formed on the semiconductor layer at least in part and separated from 7 the data line; 8 a first passivation layer formed on the data line and the drain electrode and having a 9 contact hole exposing the drain electrode at least in part; 10 11 a pixel electrode formed on the first passivation layer and connected to the drain electrode through the contact hole; and 12 a protrusion formed on the first passivation layer and disposed in the cutout at least in 13 part. 14 15. The thin film transistor array panel of claim 14, further comprising a storage electrode line overlapping the pixel electrode. 2 16. 1 The thin film transistor array panel of claim 15, wherein the storage electrode line
- 17. The thin film transistor array panel of claim 15, wherein the storage electrode line comprises a branch overlapping the cutout.

comprises an expansion overlapping the drain electrode.

2

- 18. The thin film transistor array panel of claim 14, wherein the data line is curved.
- 19. The thin film transistor array panel of claim 14, further comprising a spacer
- having a height larger than the protrusion and disposed on the same layer as the protrusion.
- 1 20. The thin film transistor array panel of claim 19, wherein the protrusion and the 2 spacer comprise organic material.
- 1 21. The thin film transistor array panel of claim 14, further comprising a color filter 2 disposed between the first passivation layer and the protrusion and the pixel electrode.
- The thin film transistor array panel of claim 21, further comprising a second passivation layer formed on the color filter and the protrusion and the pixel electrode.
- 1 23. The thin film transistor array panel of claim 1, wherein the semiconductor layer 2 has substantially the same planar shape as the data line and the drain electrode.
- 1 24. A liquid crystal display comprising:
- 2 a first substrate;

1

- a gate line formed on the first substrate;
- a data line intersecting the gate line;
- a thin film transistor connected to the gate line and the data line;
- a pixel electrode connected to the thin film transistor and having a first cutout;
- 7 a second substrate facing the first substrate;

- a common electrode formed on the second substrate and having a second cutout; and
- a first protrusion disposed in at least one of the first and the second cutouts at least in
- 10 part.
- 1 25. The liquid crystal display of claim 24, further comprising:
- a light blocking member disposed on one of the first and the second substrates; and
- a color filter disposed on one of the first and the second substrates.
- 1 26. The liquid crystal display of claim 24, further comprising a second protrusion
- 2 disposed on the data line.
- The liquid crystal display of claim 24, wherein the first cutout does not overlap
- the second cutout.